Inventor(s): Ren-Guey Hsieh Serial No.: To Be Assigned

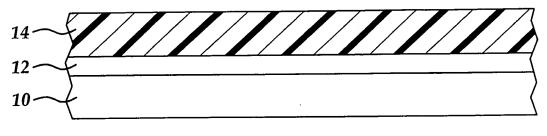
Filed: Herewith

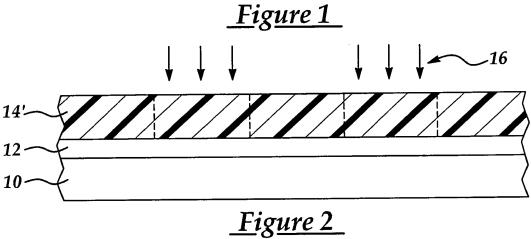
For: Gap Forming Pattern Fracturing Method ... Masking Layer

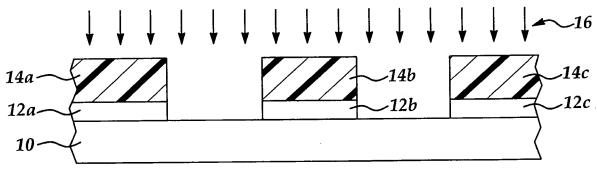
Attorney Docket No.: 67,200-447



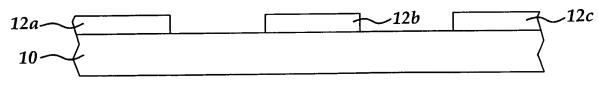
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<u>Figure 4</u>

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For: Gap Forming Pattern Fracturing Method ... Masking Layer

Attorney Docket No.: 67,200-447

